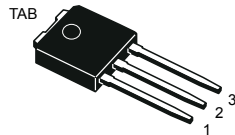
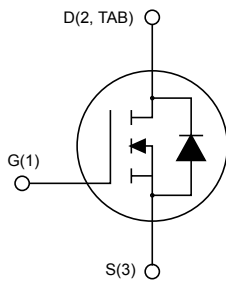


N-channel 600 V, 0.89 Ω typ., 4.5 A, MDmesh II Power MOSFET in an IPAK package


IPAK


AM01475v1_noZen


Product status

STU7LNM60N

Product summary

Order code	STU7LNM60N
Marking	7LNM60N
Package	IPAK
Packing	Tube

Features

Type	V_{DS}	$R_{DS(on)}$ max.	I_D
STU7LNM60N	600 V	0.99 Ω	4.5 A

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	600	V
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	4.5	A
	Drain current (continuous) at $T_C = 100\text{ °C}$	2.9	
$I_{DM}^{(1)}$	Drain current pulsed	18	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ °C}$	45	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
T_J	Operating junction temperature range	-55 to 150	°C
T_{stg}	Storage temperature range		

1. Pulse width limited by safe operating area.

2. $I_{SD} \leq 4.5\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS\text{ peak}} \leq V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	2.78	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient	100	°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by $T_J\text{ max}$)	2	A
E_{AS}	Single-pulse avalanche energy (starting $T_J = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	119	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On-/off-states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 600\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 600\text{ V}$ $T_C = 125\text{ °C}^{(1)}$			100	μA
I_{GSS}	Gate body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 2.5\text{ A}$		0.89	0.99	Ω

1. Defined by design, not subject to production test.

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	-	363	-	pF
C_{oss}	Output capacitance		-	24.6	-	pF
C_{rss}	Reverse transfer capacitance		-	1.1	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }480\text{ V}$, $V_{GS} = 0\text{ V}$	-	130	-	pF
R_g	Intrinsic gate resistance	$f = 1\text{ MHz}$, open drain	-	5.4	-	Ω
Q_g	Total gate charge	$V_{DD} = 480\text{ V}$, $I_D = 5\text{ A}$	-	14	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 0\text{ to }10\text{ V}$	-	2.7	-	nC
Q_{gd}	Gate-drain charge	(see Figure 13. Test circuit for gate charge behavior)	-	7.7	-	nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 2.5\text{ A}$,	-	7.2	-	ns
t_r	Rise time	$R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	10.3	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 12. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	26.4	-	ns
t_f	Fall time		-	12.6	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		4.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		18	A
$V_{SD}^{(2)}$	Forward on-voltage	$I_{SD} = 5\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 5\text{ A}$, $V_{DD} = 60\text{ V}$,	-	213		ns
Q_{rr}	Reverse recovery charge	$di/dt = 100\text{ A}/\mu\text{s}$	-	1.5		μA
I_{RRM}	Reverse recovery current	(see Figure 14. Test circuit for inductive load switching and diode recovery times)	-	14		A
t_{rr}	Reverse recovery time	$I_{SD} = 5\text{ A}$, $V_{DD} = 60\text{ V}$,	-	265		ns
Q_{rr}	Reverse recovery charge	$di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 150\text{ }^\circ\text{C}$	-	1.8		μA
I_{RRM}	Reverse recovery current	(see Figure 14. Test circuit for inductive load switching and diode recovery times)	-	14		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

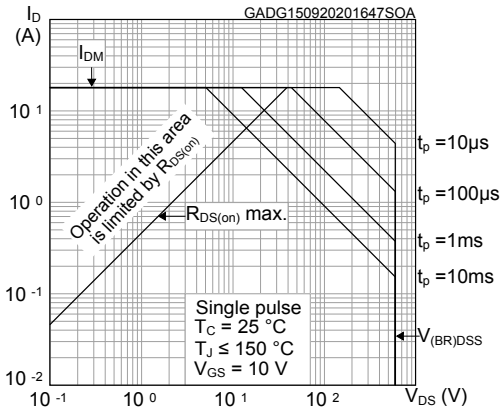


Figure 2. Thermal impedance

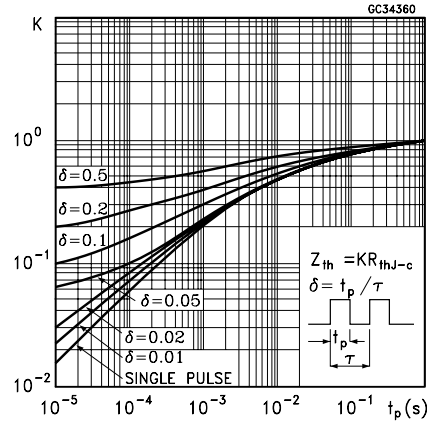


Figure 3. Output characteristics

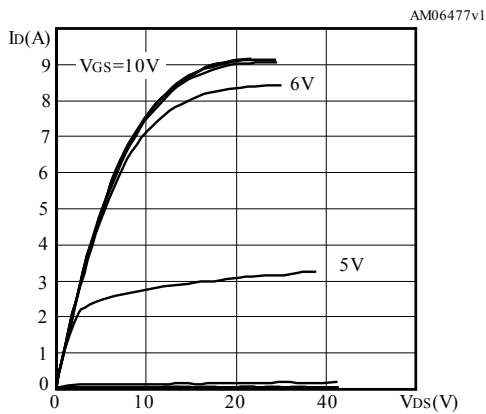


Figure 4. Transfer characteristics

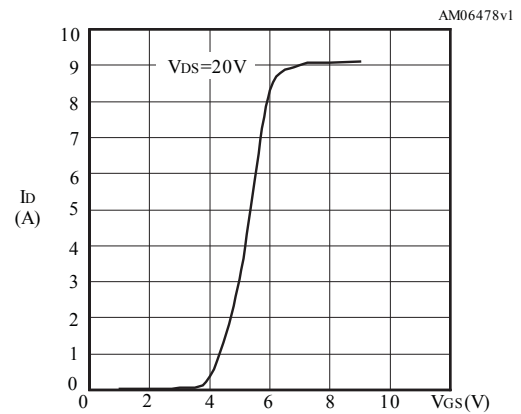


Figure 5. Gate charge vs gate-source voltage

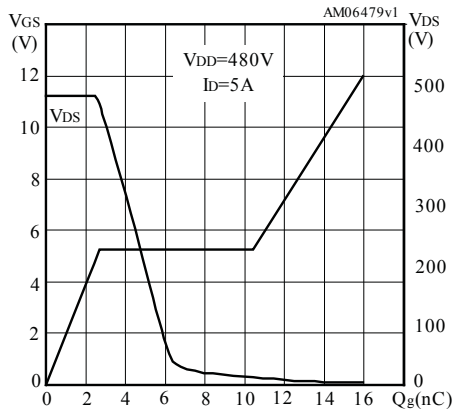


Figure 6. Static drain-source on-resistance

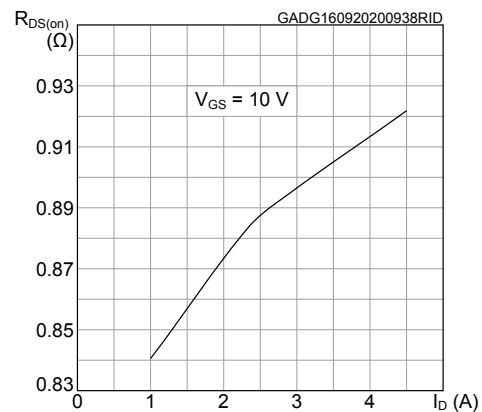


Figure 7. Capacitance variations

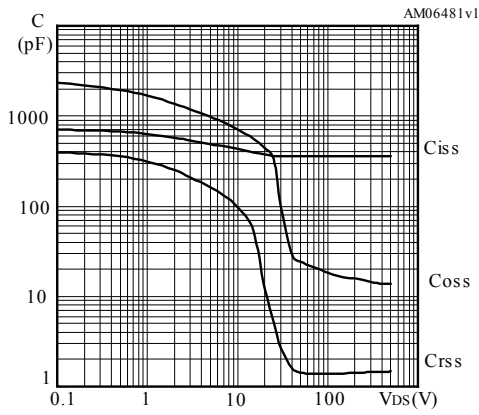


Figure 8. Output capacitance stored energy

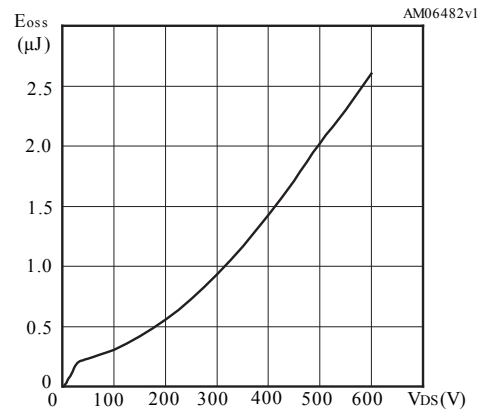


Figure 9. Normalized gate threshold voltage vs temperature

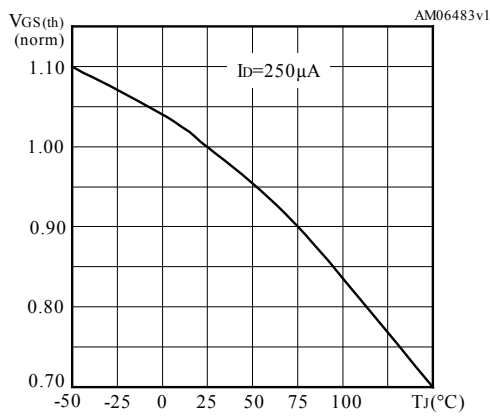


Figure 10. Normalized on-resistance vs temperature

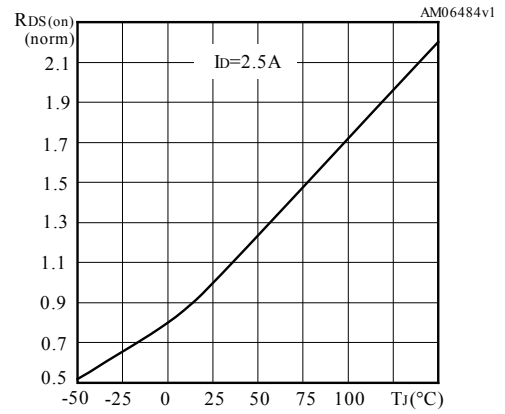
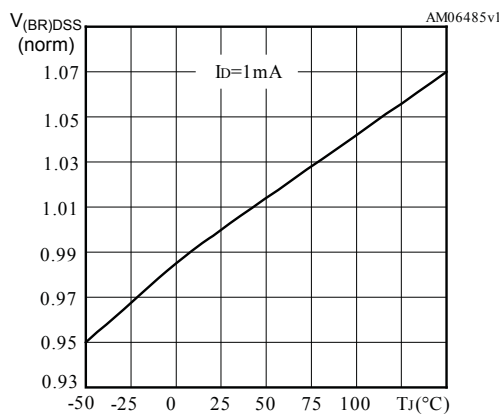


Figure 11. Normalized V_{(BR)DSS} vs temperature



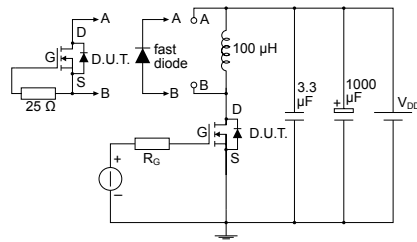
3 Test circuits

Figure 12. Test circuit for resistive load switching times


AM01468v1

Figure 13. Test circuit for gate charge behavior


AM01469v1

Figure 14. Test circuit for inductive load switching and diode recovery times


AM01470v1

Figure 15. Unclamped inductive load test circuit


AM01471v1

Figure 16. Unclamped inductive waveform


AM01472v1

Figure 17. Switching time waveform

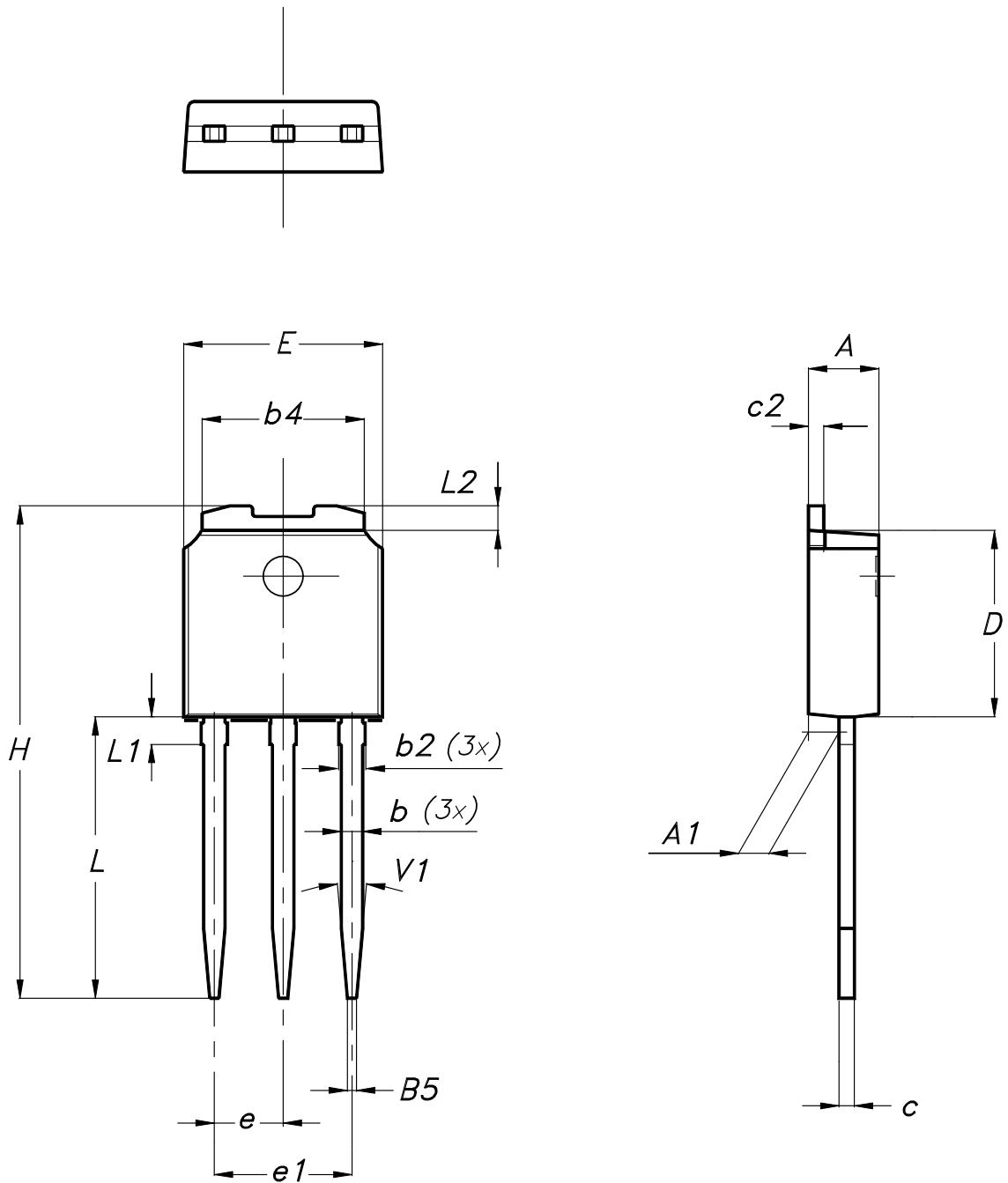

AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 IPAK (TO-251) type A package information

Figure 18. IPAK (TO-251) type A package outline



0068771_IK_typeA_rev15

Table 8. IPAK (TO-251) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.35
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.15
E	6.40		6.55
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

Revision history

Table 9. Document revision history

Date	Version	Changes
18-Sep-2020	1	First release.

Contents

1	Electrical ratings	2
2	Electrical characteristics	3
2.1	Electrical caharacteristics (curves)	5
3	Test circuits	7
4	Package information	8
4.1	IPAK (TO-251) type A package information	8
	Revision history	10

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST’s terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers’ products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, please refer to www.st.com/trademarks. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2020 STMicroelectronics – All rights reserved